PCN Numb	er:	202302	208001.2 <mark>A</mark>		PCN Dat		February 09, 2023			
Title:	Qualification for select de		as an additio	nal Fab	site and	d CD-PR wa	afer Prol	be site options		
Customer	Contact:	<u>PCN</u>	<u>Manager</u>			Dept:		uality Services		
Proposed 1s	st Ship Date:	Aug	9, 2023		-	ple reques pted until:		lar 9, 2023*		
*Sample r	equests rece	eived aft	er March 9,	2023 v	vill not	be suppo	rted.			
Change Ty	pe:									
Assemt			Desig			Wafer Bump Site				
	oly Process		Data S			Wafer Bump Material				
	oly Materials			umber c	hange			ump Process		
	nical Specifica		Test S			Wafer Fab Site				
	g/Shipping/La	beling		Test Process Wafer Fab Materia						
				COL Data ila						
PCN Details Description of Change:										
-					c			- de la compañía de l		
Revision A is to update the Assembly Construction differences table in the Description of change section. The corrections are noted below and are in bold yellow highlight.										
change section. The confections are noted below and are in bold yellow highlight.										
Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source and CD-PR as an additional probe site option for the selected devices listed in the "Product Affected" section.										
	Current	Site				Additional Site				
Current Fab Site	Process	Probe Site	Wafer Diameter	Additi Fab S		Process	Prob Site	-		
MIHO	LBC7	CLARK- PR	200 mm	RFA	В	LBC7 CD		R 300 mm		
Assembly c	onstruction di	fferences	BOM option	s are as	follows	:				
г				-						
_			<mark>Curre</mark>	nt		New				
	Die Attach I	<mark>1ate ria l</mark>	42084	58		4224264				
L										
Test covera	ge, insertions	, conditio	ons will rema	in consis	stent wi	th current	testing.			
Reason for	Change:									
Continuity of	of Supply									
Anticipate	d impact on	Form, F	it, Function	, Quality	y or Re	liability (oositive	e / negative):		
None										
Changes to	product ide	entificat	ion resultin	g from	this PC	:N:				
Fab Site Informati	on:									
		Chip Sit	e Origin Cod	e Ch	ip Site	Country Co	de			
Chi	o Site		(20L)		•	21L)		Chip Site City		
MI	HO8		MH8		•	JPN		Ibaraki		
	AB		RFB			USA		Richardson		
Sample pro	duct shipping	label (no	t actual proc	luct labe	el)					

UBL: 5A (L)TO	39	(31T)LOT: 39590 (4W) TKY(1T) 75 (P) (2P) REV: (20L) CS0: SHE (21L (22L) AS0: MLA (23L	0033217
Due duet Affe ste de			
Product Affected:			1
Product Affected: TAS6424EQDKQRQ1	TAS6424LSQDKQRQ1	TAS6424MSQDKQRQ1	TAS6424QDKQRQ1

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approve Date 28-DECEMBER -2022

					Data Di	splayed as: N	umber	of lots / Total sar	mple size / Tota	al failed				
Type #	Test Spec		Test Name	Condi	tion Duration	Qual Device: TAS6424XQDKC		Qual Device: TAS6424XQDKQRQ:	Qual Device: <u>TAS6424XQD</u>	<u>KQRQ1</u>	Produc Refe	QBS t/Package erence: 4QDKQRQ1	QBS Package Reference: <u>TAS6424QDKQRQ1</u>	QBS Process Reference: <u>TPS2543QRTETQ1</u>
Test Group	A - Accel	erated Environn	ent Stres	s Tests										
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL2 260C	1 Step	-	-		-	-	-	3/Pass
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL3 260C	1 Step	1/Pass	-	3/F	ass	3/Pass	-	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	-		-	3/231/0	-	3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	1/77/0	-		-	3/231/0		3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/2	31/0	-	-	-
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	-	3/2	31/0	3/231/0	-	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	1/	5/0	-		
PTC	A5	JEDEC JESD22-A105	1	45	PTC	-40/125C	1000 Cycles	1/45/0	-		-	-	1/45/0	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/45/0	-	3/1	35/0	-	3/135/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-			-	-	3/135/0
Test Group	B - Accel	erated Lifetime	Simulation	n Tests										
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	1/77/0	-		-	2/154/0	-	3/231/0

Qualification Results

							48						
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	-			-	3/2400/0
Test Group	p C - Pack	age Assembly Inte	egrity Te	sts									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	2/60/0	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	2/60/0	3/90/0	3/90/0	3/90/0
SD	СЗ	JEDEC J-STD- 002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	1/15/0	-	-
SD	СЗ	JEDEC J-STD- 002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	1/15/0	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	1/10/0	2/20/0	3/30/0	3/30/0	3/30/0
Test Group D - Die Fabrication Reliability Tests													
ЕМ	D1	JESD61			Electromigration	-	-	Completed Per Process Technology Requirements					
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements					
нсі	D3	JESD60 & 28			Hot Carrier Injection	-	-	Completed Per Process Technology Requirements					
NBTI	D4	-			Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements					
SM	D5	-			Stress Migration	-	-	Completed Per Process Technology Requirements					
Test Group	p E - Elect	rical Verification T	ests										
ESD	E2	AEC Q100-002	1	з	ESD HBM	-	2000 Volts	1/3/0	1/3/0	-		-	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	750 Volts	1/3/0	1/3/0	-			1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	-	-	-	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	2/60/0	1/30/0		-		3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
 The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
 The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
 Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

- QBS: Qual By Similarity
- Qual Device TAS6424XQDKQRQ1 is qualified at MSL3 260C
- Qual Device TAS6424XQDKQRQ1 is qualified at MSL3 260C
- Qual Device TAS6424XQDKQRQ1 is qualified at MSL3 260C

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approve Date 12-JANUARY -2023

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Name	Condition	Duration	Qual Device: <u>TAS6424XQDKQRQ1</u>	Qual Device: <u>TAS6424LQDKQRQ1</u>	Qual Device: TAS6424MQDKQRQ1	Qual Device: TAS6424LSQDKQRQ1	QBS Reference: TAS6424QDKQRQ1	QBS Reference: TAS6424QDKQRQ1	QBS Reference: TPS2543QRTETQ1
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	-	-	-	3/231/0	3/231/1	3/231/0
UHAST	A3	Autoclave	130C/85%RH	96 Hours	-	-	-	-	3/231/0	-	3/231/0
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	3/231/0	-	-	-	-	-	-
тс	A4	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	-	-	-	3/231/0	3/231/2	3/231/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	3/135/0	-	-	-	-	3/135/0	
HTSL	A6	High Temperature Storage Life	175C	500 Hours	-	-	-	-		-	3/135/0
HTOL	81	Life Test	125C	1000 Hours	-	-	-	-	2/154/0	-	3/231/0
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	-	-	-	-	-	3/2400/0
SD	C3	PB Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	-	-	-	1/15/0	-	-
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	-	-	-	1/15/0	-	1/15/0
PD	C4	Physical Dimensions	Cpk>1.67	-	-	-	-	-	3/30/0	3/30/0	3/30/0
ESD	E2	ESD CDM	-	500 Volts			-	-	-	-	1/3/0
ESD	E2	ESD HBM	-	2000 Volts			-	-	-	-	1/3/0
LU	E4	Latch-Up	Per JESD78	-	-	-	-	-	-	-	1/6/0
CHAR	E5	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	-	-	-	-	-	-	3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

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Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

- QBS: Qual By Similarity
- Qual Device TAS6424XQDKQRQ1 is qualified at MSL3 260C
- Qual Device TAS6424LQDKQRQ1 is qualified at MSL3 260C
 Qual Device TAS6424MQDKQRQ1 is qualified at MSL3 260C
- Qual Device TAS6424MQDKQRQ1 is qualified at MSL3 260C
 Qual Device TAS6424LSQDKQRQ1 is qualified at MSL3 260C
- Qual Device 1A30424E3QDRQRQE1s qualified at MSE3 2000

Affected ZVEI IDs: SEM-PW-13, SEM-PW-02, SEM-TF-01

For questions regarding this notice, e-mails can be sent to the contact below or your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	PCN ww admin team@list.ti.com

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